single poly-Si JL-FinFET GAA-NWs

$W_{\text{eff}} = (100\text{nm} \times 2 + 9\text{nm} \times 2) \times 10$

$W_2 = 6 \mu m$

$L = 1 \mu m$

FN programmed:

- $V_g = 23V, t_p = 1s$ at $200^\circ C$
- $V_g = 23V, t_p = 1s$ at $150^\circ C$
- $V_g = 23V, t_p = 1s$ at $120^\circ C$
- $V_g = 23V, t_p = 1s$ at $85^\circ C$
- $V_g = 20V, t_p = 1ms$ at $85^\circ C$
- $V_g = 17V, t_p = 1ms$ at $85^\circ C$